

/ Descriptions

SOT-23 PNP Silicon PNP transistor in a SOT-23 Plastic Package.

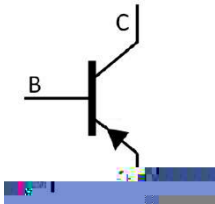
/ Features

Low saturation voltage, large collector current.

/ Applications

General purpose amplifier and muting switch application.

/ Equivalent Circuit



/ Pinning



PIN1 Base PIN 2 Emitter PIN 3 Collector

/ h_{FE} Classifications & Marking

h_{FE} Classifications
Symbol

/ Absolute Maximum Ratings(Ta=25)

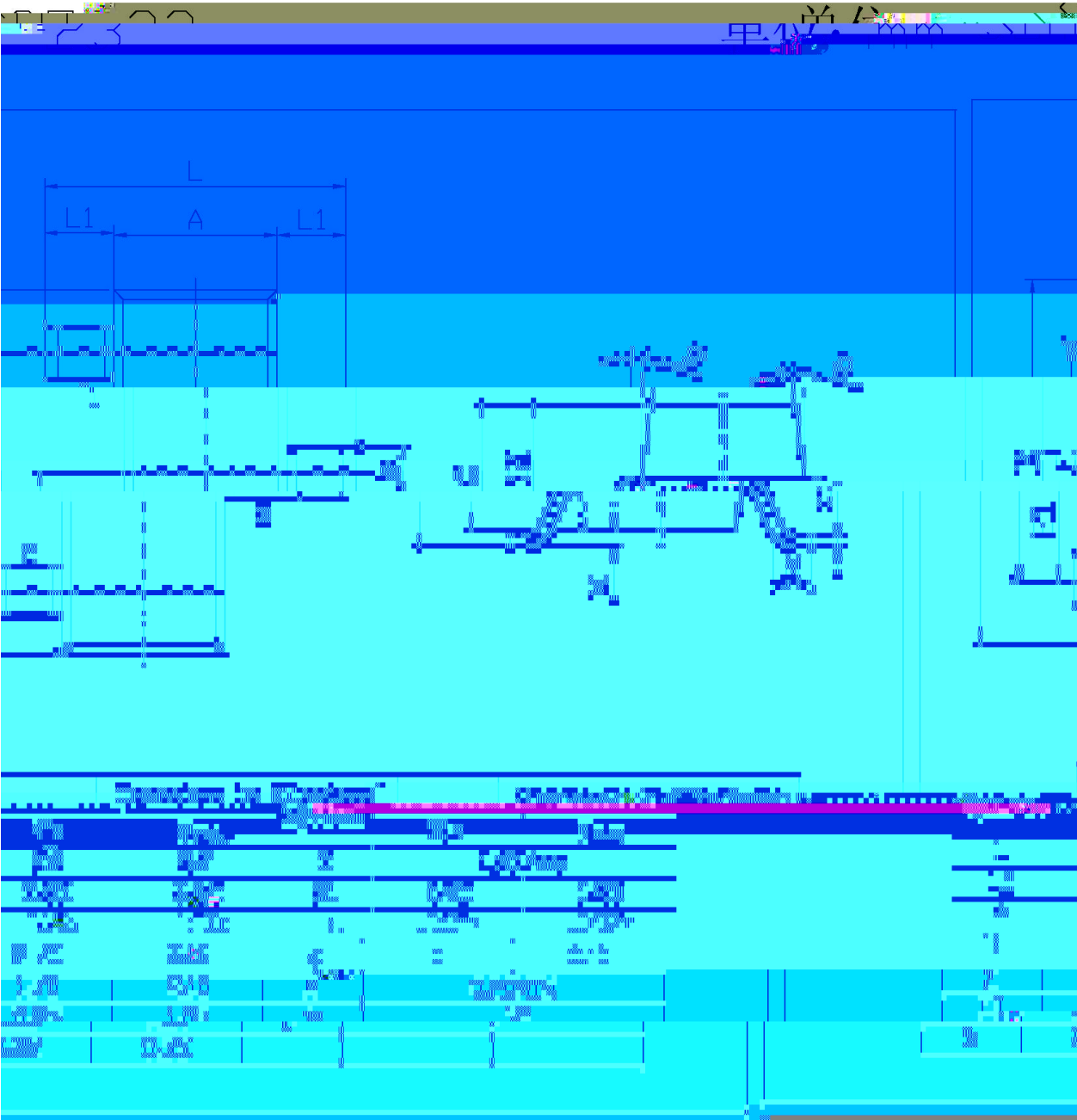
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-15	V
Collector to Emitter Voltage	V_{CEO}	-12	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current	I_C	-400	mA
Base Current	I_B	-50	mA
Collector Power Dissipation	P_C	100	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

/ Electrical Characteristics(Ta=25)

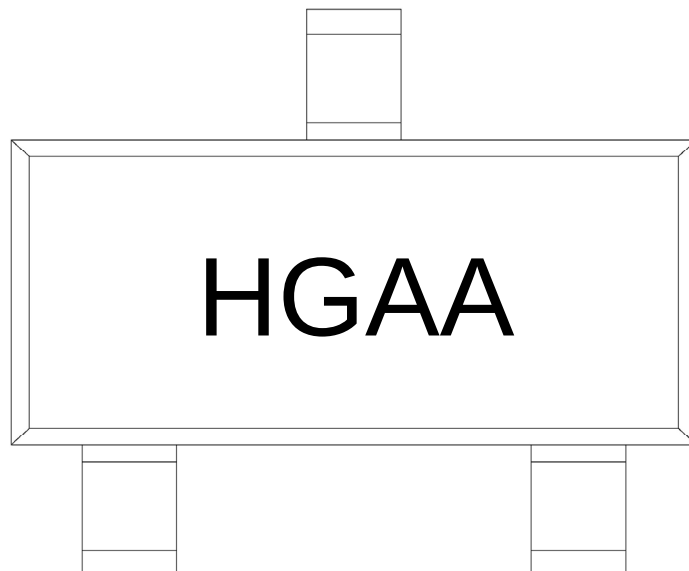
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cut-Off Current	I_{CBO}	$V_{CB}=-15V$ $I_E=0$			-0.1	μA
Emitter Base Cut-Off Current	I_{EBO}	$V_{EB}=-5.0V$ $I_C=0$			-0.1	μA
DC Current Gain	h_{FE}	$V_{CE}=-2.0V$ $I_C=-10mA$	300		1000	
Collector to Emitter Saturation Voltage	$V_{CE(sat)(1)}$	$I_C=-10mA$ $I_B=-0.5mA$		-0.015	-0.03	V
	$V_{CE(sat)(2)}$	$I_C=-200mA$ $I_B=-10mA$		-0.11	-0.25	V
Base to Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=-200mA$ $I_B=-10mA$		-0.87	-1.2	V
Transition Frequency	f_T	$V_{CE}=-2.0V$ $I_E=-10mA$	80	130		MHz
Collector Output Capacitance	C_{ob}	$V_{CB}=-10V$ $I_E=0$ $f=1.0MHz$		4.2		pF
Collector-Emitter On Resistance	R_{on}	$I_B=-1.0mA$ $V_{in}=-1.0V$ $V_{rms}f=1KHz$		0.9		Ω
Switching time	Turn-On Time	$I_{B1}=-I_{B2}=5.0mA$		40		ns
	Storage Time			280		
	Fall Time			45		

/ Electrical Characteristic Curve

/ Package Dimensions



/ Marking Instructions



H

GA

A: h_{FE}

Note:

H: Company Code.

GA: Product Type Code

A: h_{FE} Classifications Symbol Code

() / Temperature Profile for IR Reflow Soldering(Pb Z